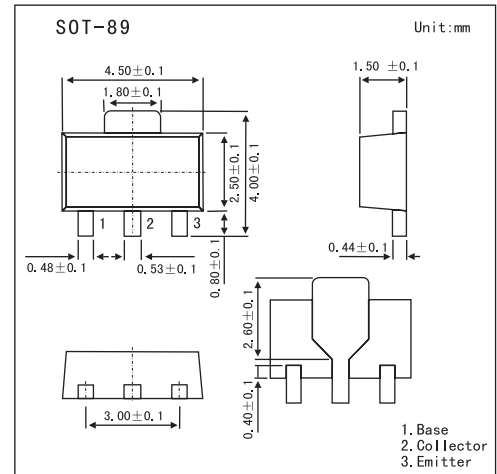


Power Transistor

2SB1427

■ Features

- Low saturation voltage,
typically $V_{CE(sat)} = -0.5V$ at $I_C/I_B = -1A/-50mA$.
- Excellent DC current gain characteristics.

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-2	A
Collector current(Pulse)	I_{CP}^*	-3	A
Collector power dissipation	P_C	0.5	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* Single pulse, $P_w=10ms$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	$I_C = -50\mu A$	-20			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C = -1mA$	-20			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = -50\mu A$	-6			V
Collector cutoff current	I_{CBO}	$V_{CB} = -16V$			-0.5	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5V$			-0.5	μA
DC current transfer ratio	$V_{CE(sat)}$	$I_C = -1A, I_B = -500mA$			-0.5	V
Collector-emitter saturation voltage	h_{FE}	$V_{CE} = -6V, I_C = -0.5A$	390		820	
Transition frequency	C_{ob}	$V_{CE} = -10V, I_E = 10mA, f = 30MHz$		90		MHz
Output capacitance	f_T	$V_{CB} = -10V, I_E = 0A, f = 1MHz$		30		pF

■ Marking

Marking	BJE
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